

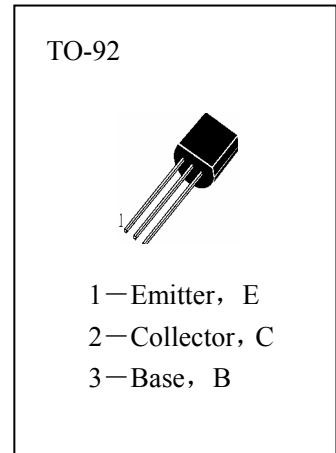


■ APPLICATIONS

power amplifier Applications, power Switching Applications.

■ ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

- T_{stg}—Storage Temperature..... -55~150°C
- T_j—Junction Temperature.....150°C
- P_C—Collector Dissipation.....750mW
- V_{CBO}—Collector-Base Voltage.....50V
- V_{CEO}—Collector-Emitter Voltage.....50V
- V_{EBO}—Emitter-Base Voltage.....5V
- I_C—Collector Current.....2A
- I_b—Base Current.....-0.5A



■ ELECTRICAL CHARACTERISTICS (T_a=25°C)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV _{CBO}	Collector-Base Breakdown Voltage	50			V	I _C =100 μ A, I _E =0
BV _{CEO}	Collector-Emitter Breakdown Voltage	50			V	I _C =10mA, I _B =0
BV _{EBO}	Emitter-Base Breakdown Voltage	5			V	I _E =100 μ A, I _C =0
I _{CBO}	Collector Cut-off Current			1.0	μ A	V _{CB} =50V, I _E =0
I _{EBO}	Emitter Cut-off Current			1.0	μ A	V _{EB} =5V, I _C =0
HFE(1)	DC Current Gain	70		240		V _{CE} =2V, I _C =0.5A
HFE(2)		40				V _{CE} =2V, I _C =1.5A
V _{CE(sat)}	Collector- Emitter Saturation Voltage			0.5	V	I _C =1A, I _B =50mA
V _{BE(sat)}	Base-Emitter Saturation Voltage			1.2	V	I _C =1A, I _B =50mA
f _T	Current Gain-Bandwidth Product		100		MHz	V _{CE} =2V, I _C =0.5A
C _{ob}	Output Capacitance		30		pF	V _{CB} =10V, I _E =0, f=1MHz
t _{ON}	Turn-on Time		0.1		μ S	
t _{STG}	Storage Time		1.0		μ S	See specified test circuit
t _F	Fall Time		0.1		μ S	

■ hFE Classification

O	Y
70—140	120—240

